

Application Serial No. 10/738,397
Reply to office action of August 10, 2006

PATENT
Docket: CU-3496

Amendments To The Claims

The listing of claims presented below will replace all prior versions, and listings, of claims in the application.

Listing of claims:

1. (currently amended) A method for fabricating a semiconductor device, which comprises the steps of:

forming a gate line on a semiconductor substrate;

forming successively a buffer layer ~~and~~, a spacer nitride film, and a spacer oxide film on the entire surface of the substrate including the gate line;

selectively etching the buffer layer and the spacer nitride film in such a manner that they remain on both sides of the gate line;

performing an ion implantation process using the remaining buffer layer and spacer nitride film as a barrier film to form junction regions in the semiconductor substrate at both sides of the gate line;

subjecting the entire upper portion of the substrate including the junction regions to a rapid thermal annealing (RTA) process;

forming an interlayer insulating film on the entire upper portion of the resulting substrate;

selectively removing the interlayer insulating film to form contact holes exposing the upper surface of the junction regions; and

forming contact plugs in the contact holes.

Application Serial No. 10/738,397
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PATENT
Docket: CU-3496

2. (canceled)
3. (currently amended) The method of claim ~~[[2]]~~ 1, wherein the buffer layer is in the form of a laminated structure of an oxide film and a nitride film, a single-layered oxide film, or a single-layered nitride film.
4. (currently amended) The method of claim ~~[[2]]~~ 1, wherein the spacer nitride film is formed to a thickness of 100-700 Å.
5. (currently amended) The method of claim ~~[[2]]~~ 1, wherein the ion implantation process is performed using a given tilt angle and a given number of rotations.
6. (original) The method of claim 5, wherein the tilt angle is 0 to 30° and the number of rotations is 2 to 4.
7. (canceled)
8. (original) The method of claim 1, which additionally comprises the step of performing a rapid thermal annealing (RTA) process after the step of forming the interlayer insulating film.
9. (original) The method of claim 1, which additionally comprises the step of

Application Serial No. 10/738,397
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PATENT
Docket: CU-3496

subjecting the interlayer insulating film to a reflow annealing process and a rapid thermal annealing process after the step of forming the interlayer insulating film.

10. (original) The method of claim 1, which additionally comprises the step of performing a high temperature rapid thermal annealing process before forming the contact plugs, and the step of a low temperature rapid thermal annealing process after forming the contact plugs.

11. (currently amended) The method of any of claim 8, ~~9 and 10~~, wherein the buffer layer is in the form of a laminated structure of an oxide film and a nitride film, a single-layered oxide film, or a single-layered nitride film.

12. (currently amended) The method of any of claim 8, ~~9 and 10~~, wherein the spacer nitride film is formed to a thickness of more than 90 Å.

13. (currently amended) The method of any of claim 8, ~~9 and 10~~, wherein the ion implantation process is performed using a given tilt angle and a given number of rotations.

14. (original) The method of claim 13, wherein the tilt angle is 0 to 30° and the number of rotations is 2 to 4.

15. (canceled)

Application Serial No. 10/738,397
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PATENT
Docket: CU-3496

16. (new) The method of Claim 9, wherein the buffer layer is in the form of a laminated structure of an oxide film and a nitride film, a single-layered oxide film, or a single-layered nitride film.
17. (new) The method of claim 9, wherein the sapacer nitride film is formed to a thickness of more than 90 Å.
18. (new) The method of Claim 9, wherein the ion implantation process is performed using a given tilt angle and given number of rotations.
19. (new) The method of claim 18, wherein the tilt angle is 0 to 30 ° and the number of rotations is 2 to 4.
20. (new) The method of claim 10, wherein the buffer layer is in the form of a laminated structure of an oxide film and a nitride film, a single-layered oxide film, or a single-layered nitride film.
21. (new) The method of claim 10, wherein the spacer nitride film is formed to a thickness of more than 90 Å.
22. (new) The method of claim 10, wherein the ion Implantation process is performed using a given tilt angle and a given number of rotations.

Application Serial No. 10/738,397
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PATENT
Docket: CU-3496

23. (new) The method of claim 22, wherein the tilt angle is 0 to 30 ° and the number of rotations is 2 to 4.